



PDTC143X/123J/143Z/114Y/124XQC-Q series

50 V, 100 mA NPN resistor-equipped transistors

Rev. 1 — 1 October 2021

Product data sheet

1. General description

100 mA NPN Resistor-Equipped Transistor (RET) family in an ultra small DFN1412D-3 (SOT8009) leadless Surface-Mounted Device (SMD) plastic package with side-wettable flanks.

Table 1. Product overview

Type number	R1	R2	Package		PNP complement:
	k Ω	k Ω	Nexperia	JEDEC	
PDTC143XQC-Q	4.7	10	SOT8009	MO-340CA	PDTA143XQC-Q
PDTC123JQC-Q	2.2	47			PDTA123JQC-Q
PDTC143ZQC-Q	4.7	47			PDTA143ZQC-Q
PDTC114YQC-Q	10	47			PDTA114YQC-Q
PDTC124XQC-Q	22	47			PDTA124XQC-Q

2. Features and benefits

- 100 mA output current capability
- Built-in resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Digital applications
- Cost saving alternative for BC847-Q series in digital applications
- Controlling IC inputs
- Switching loads

4. Quick reference data

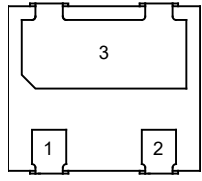
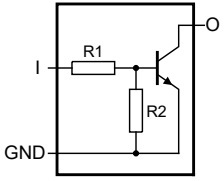
Table 2. Quick reference data

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I_O	output current		-	-	100	mA

5. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	 <p>Transparent top view</p>	 <p>aaa-019964</p>
2	GND	GND (emitter)		
3	O	output (collector)		

6. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTC143XQC-Q	DFN1412D-3	plastic leadless ultra small outline package with side-wettable flanks (SWF); 3 terminals; 0.8 mm pitch; body: 1.4 x 1.2 x 0.48 mm	SOT8009
PDTC123JQC-Q			
PDTC143ZQC-Q			
PDTC114YQC-Q			
PDTC124XQC-Q			

7. Marking

Table 5. Marking

Type number	Marking code
PDTC143XQC-Q	8P
PDTC123JQC-Q	8L
PDTC143ZQC-Q	8Q
PDTC114YQC-Q	8K
PDTC124XQC-Q	6E

8. Limiting values

Table 6. Limiting values

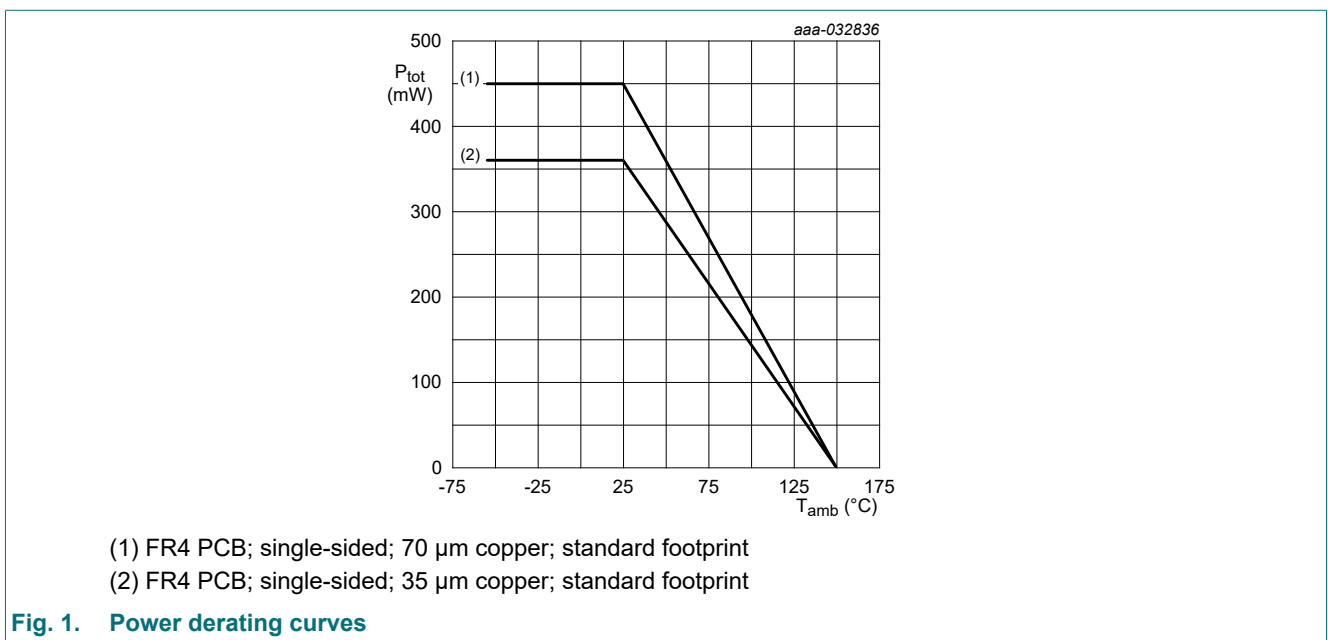
In accordance with the Absolute Maximum Rating System (IEC 60134).

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CBO}	collector-base voltage	open emitter	-	50	V	
V_{CEO}	collector-emitter voltage	open base	-	50	V	
V_{EBO}	emitter-base voltage	open collector	-	7	V	
	PDTC143XQC-Q			5	V	
	PDTC123JQC-Q			5	V	
	PDTC143ZQC-Q			6	V	
	PDTC114YQC-Q			7	V	
	PDTC124XQC-Q					
V_i	input voltage			-7	+30	V
	PDTC143XQC-Q			-5	+12	V
	PDTC123JQC-Q			-5	+30	V
	PDTC143ZQC-Q			-6	+40	V
	PDTC114YQC-Q			-7	+40	V
	PDTC124XQC-Q					
I_O	output current		-	100	mA	
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	360	mW
			[2]	-	450	mW
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-55	150	°C	
T_{stg}	storage temperature		-65	150	°C	

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided; 35 μm copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided; 70 μm copper; tin-plated and standard footprint.



(1) FR4 PCB; single-sided; 70 μm copper; standard footprint
(2) FR4 PCB; single-sided; 35 μm copper; standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 7. Thermal characteristics

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	348	K/W
			[2]	-	278	K/W

- [1] Device mounted on an FR4 PCB; single-sided; 35 μm copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided; 70 μm copper; tin-plated and standard footprint.

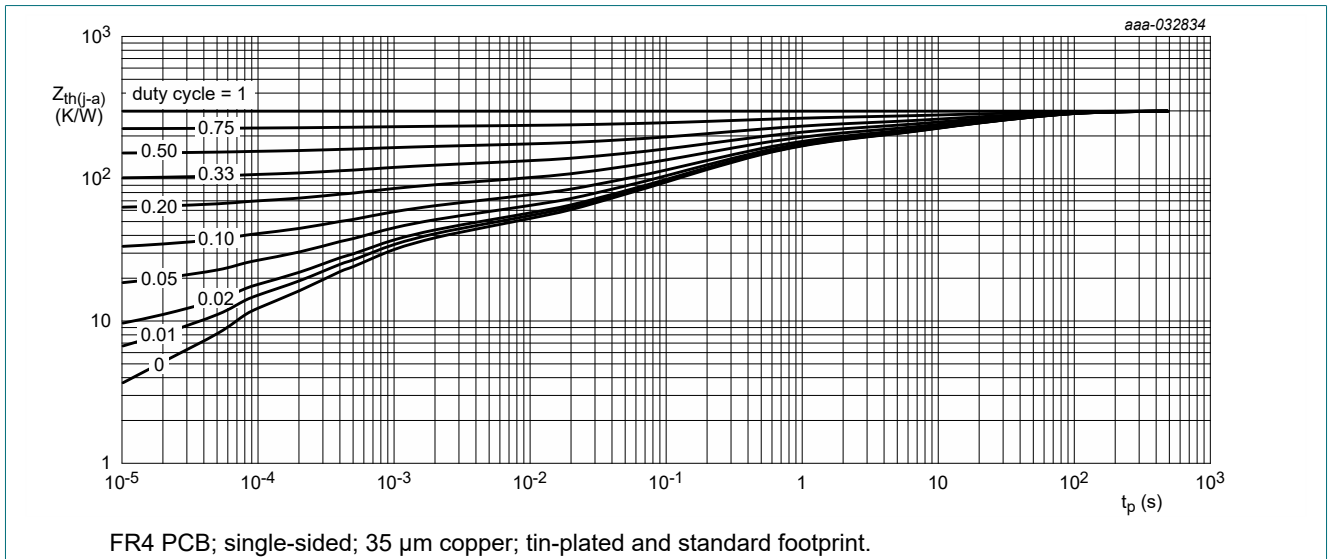


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

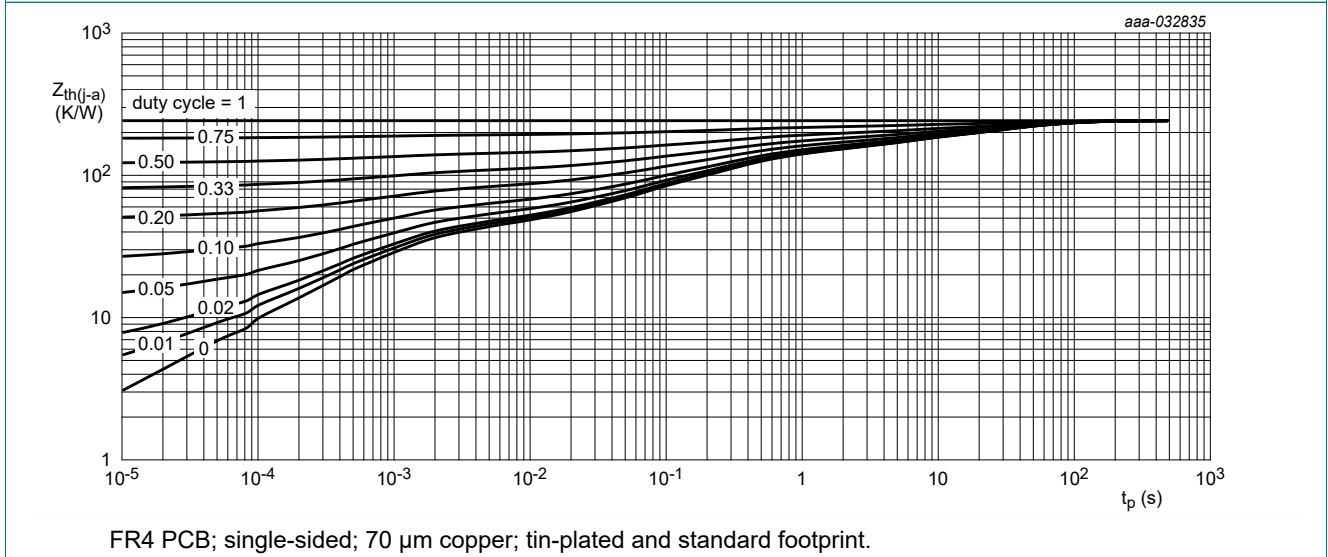


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

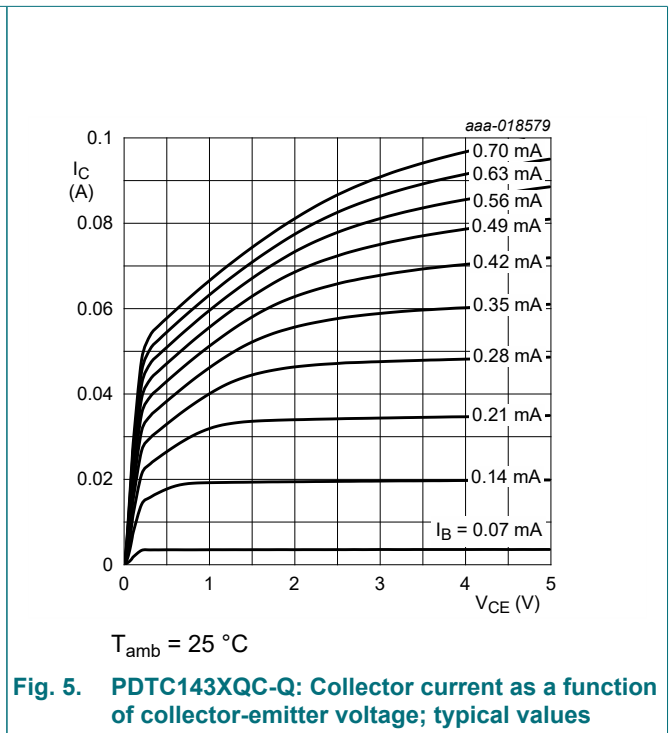
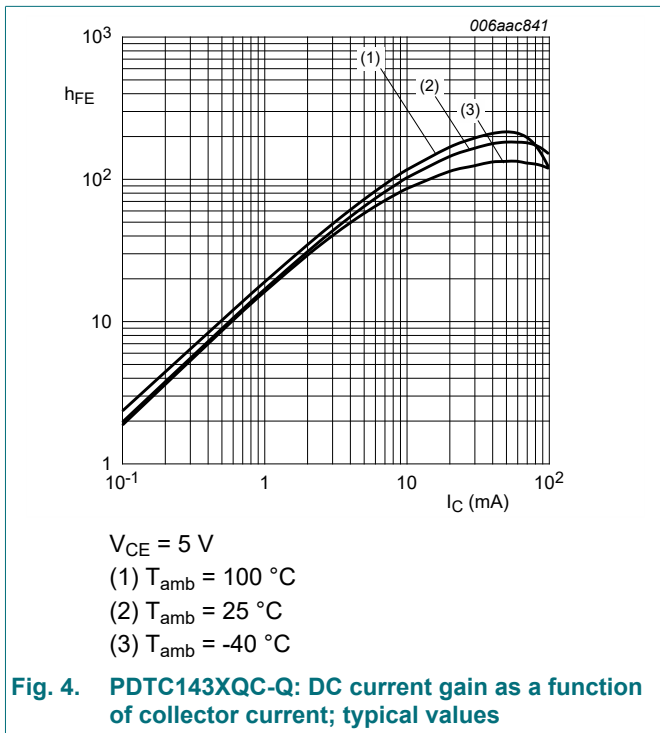
Table 8. Characteristics
 $T_{amb} = 25\text{ °C}$ unless otherwise specified.

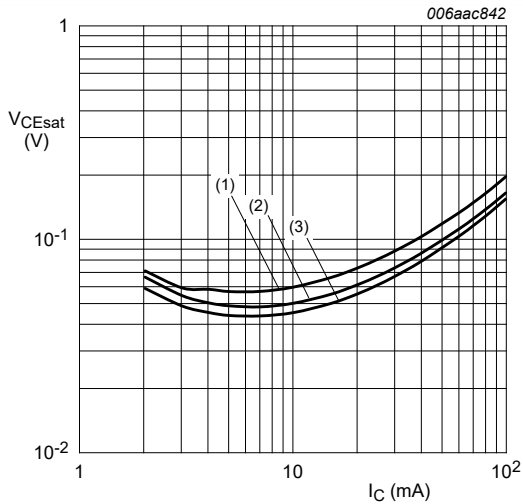
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100\ \mu\text{A}$; $I_E = 0\ \text{A}$	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2\ \text{mA}$; $I_B = 0\ \text{A}$	50	-	-	V
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\ \text{V}$; $I_E = 0\ \text{A}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\ \text{V}$; $I_B = 0\ \text{A}$	-	-	100	nA
		$V_{CE} = 30\ \text{V}$; $I_B = 0\ \text{A}$; $T_j = 150\text{ °C}$	-	-	5	μA
I_{EBO}	emitter-base cut-off current					
	PDTC143XQC-Q	$V_{EB} = 5\ \text{V}$; $I_C = 0\ \text{A}$	-	-	600	μA
	PDTC123JQC-Q		-	-	180	μA
	PDTC143ZQC-Q		-	-	170	μA
	PDTC114YQC-Q		-	-	150	μA
	PDTC124XQC-Q		-	-	120	μA
h_{FE}	DC current gain					
	PDTC143XQC-Q	$V_{CE} = 5\ \text{V}$; $I_C = 10\ \text{mA}$	50	-	-	
	PDTC123JQC-Q		100	-	-	
	PDTC143ZQC-Q		100	-	-	
	PDTC114YQC-Q	$V_{CE} = 5\ \text{V}$; $I_C = 5\ \text{mA}$	100	-	-	
	PDTC124XQC-Q		80	-	-	
V_{CEsat}	collector-emitter saturation voltage					
	PDTC143XQC-Q	$I_C = 10\ \text{mA}$; $I_B = 0.5\ \text{mA}$	-	-	100	mV
	PDTC123JQC-Q		-	-	100	mV
	PDTC143ZQC-Q	$I_C = 5\ \text{mA}$; $I_B = 0.25\ \text{mA}$	-	-	100	mV
	PDTC114YQC-Q		-	-	100	mV
	PDTC124XQC-Q	$I_C = 10\ \text{mA}$; $I_B = 0.5\ \text{mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage					
	PDTC143XQC-Q	$V_{CE} = 5\ \text{V}$; $I_C = 100\ \mu\text{A}$	-	0.8	0.3	V
	PDTC123JQC-Q		-	0.6	0.5	V
	PDTC143ZQC-Q		-	0.6	0.5	V
	PDTC114YQC-Q		-	0.7	0.5	V
	PDTC124XQC-Q		-	0.8	0.5	V
$V_{I(on)}$	on-state input voltage					
	PDTC143XQC-Q	$V_{CE} = 0.3\ \text{V}$; $I_C = 20\ \text{mA}$	2.5	1.5	-	V
	PDTC123JQC-Q	$V_{CE} = 0.3\ \text{V}$; $I_C = 5\ \text{mA}$	1.1	0.75	-	V
	PDTC143ZQC-Q	$V_{CE} = 0.3\ \text{V}$; $I_C = 5\ \text{mA}$	1.3	0.9	-	V
	PDTC114YQC-Q	$V_{CE} = 0.3\ \text{V}$; $I_C = 1\ \text{mA}$	1.4	0.8	-	V
	PDTC124XQC-Q	$V_{CE} = 0.3\ \text{V}$; $I_C = 2\ \text{mA}$	2.0	1.1	-	V

50 V, 100 mA NPN resistor-equipped transistors

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R1	bias resistor 1 (input)					
	PDTC143XQC-Q		[1] 3.3	4.7	6.1	kΩ
	PDTC123JQC-Q		1.54	2.2	2.86	kΩ
	PDTC143ZQC-Q		3.3	4.7	6.1	kΩ
	PDTC114YQC-Q		7	10	13	kΩ
PDTC124XQC-Q	15.4		22	28.6	kΩ	
R2/R1	bias resistor ratio					
	PDTC143XQC-Q		[1] 1.7	2.13	2.6	
	PDTC123JQC-Q		17	21	26	
	PDTC143ZQC-Q		8	10	12	
	PDTC114YQC-Q		3.7	4.7	5.7	
PDTC124XQC-Q	1.7		2.13	2.6		
f_T	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	[2] -	230	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	2.5	pF

- [1] See "Section 11: Test information" for resistor calculation and test conditions
- [2] Characteristics of built-in transistor

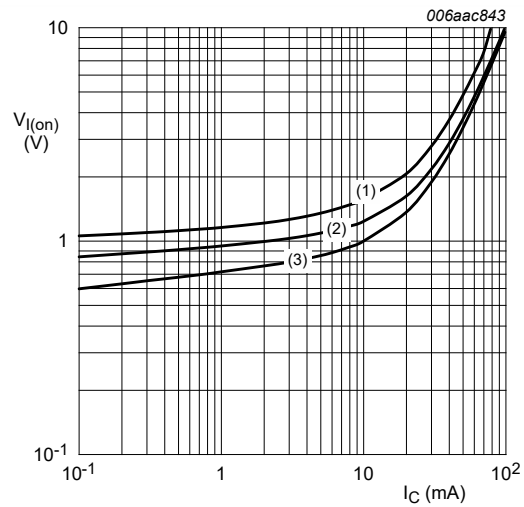




$I_C/I_B = 20$

- (1) $T_{amb} = 100\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -40\text{ °C}$

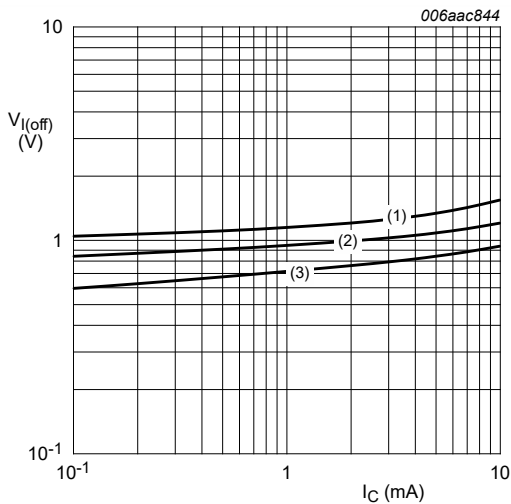
Fig. 6. PDTC143XQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$

- (1) $T_{amb} = -40\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

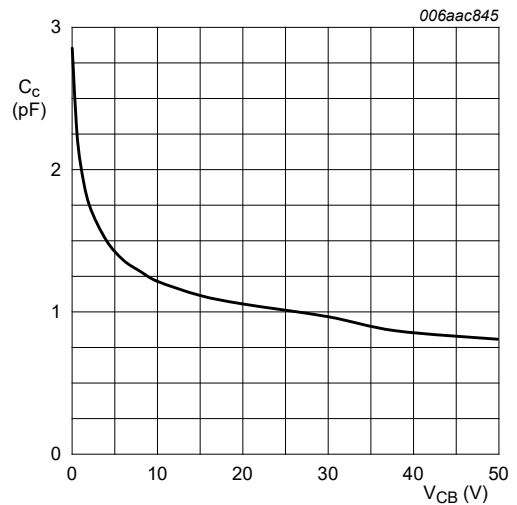
Fig. 7. PDTC143XQC-Q: On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$

- (1) $T_{amb} = -40\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

Fig. 8. PDTC143XQC-Q: Off-state input voltage as a function of collector current; typical values



$f = 1\text{ MHz}$

$T_{amb} = 25\text{ °C}$

Fig. 9. PDTC143XQC-Q: Collector capacitance as a function of collector-base voltage; typical values

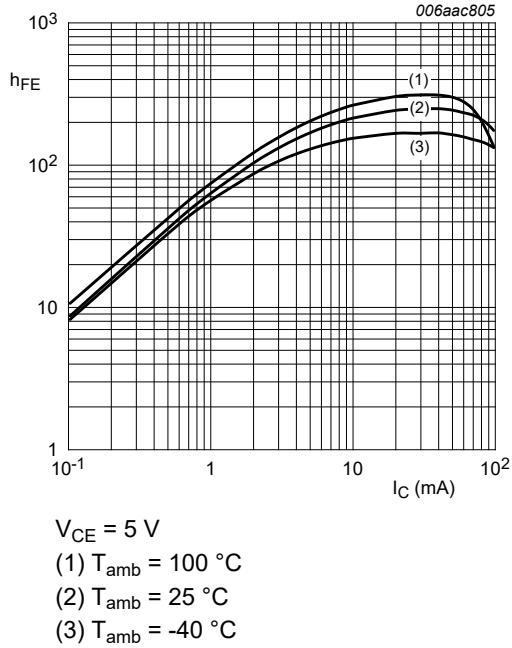


Fig. 10. PDTC123JQC-Q: DC current gain as a function of collector current; typical values

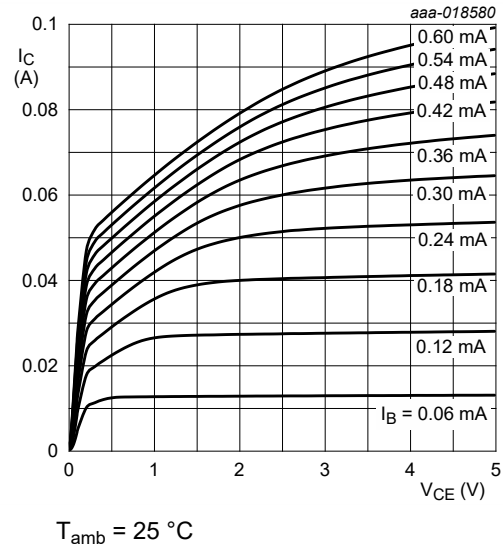


Fig. 11. PDTC123JQC-Q: Collector current as a function of collector-emitter voltage; typical values

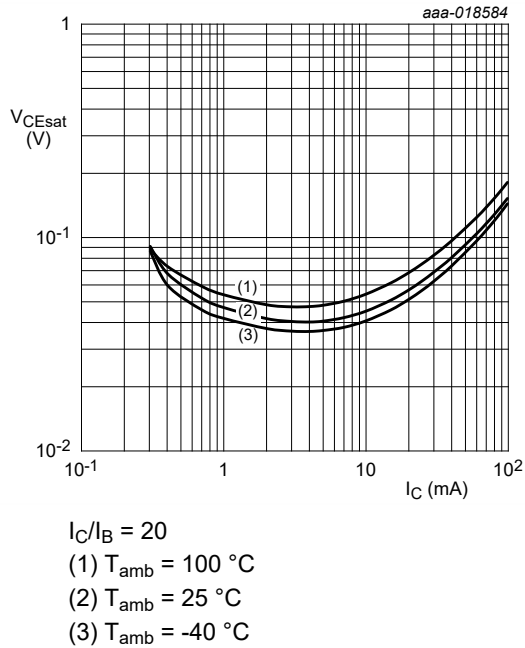


Fig. 12. PDTC123JQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values

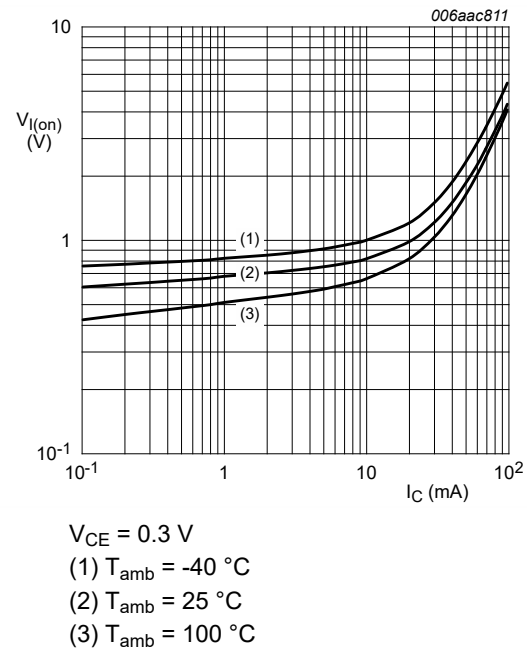


Fig. 13. PDTC123JQC-Q: On-state input voltage as a function of collector current; typical values

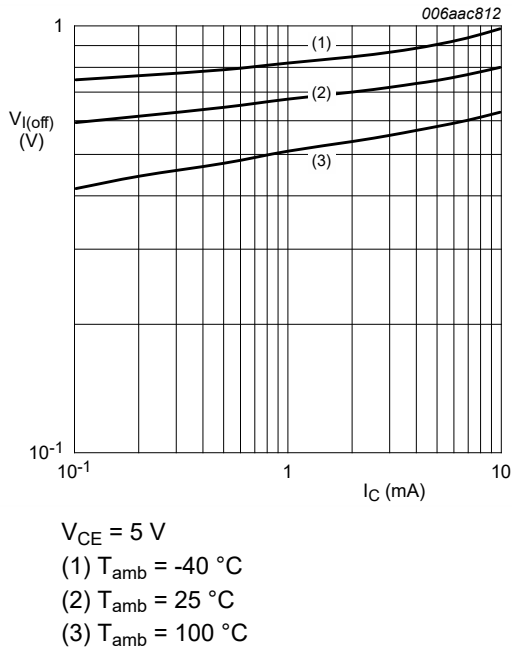


Fig. 14. PDTC123JQC-Q: Off-state input voltage as a function of collector current; typical values

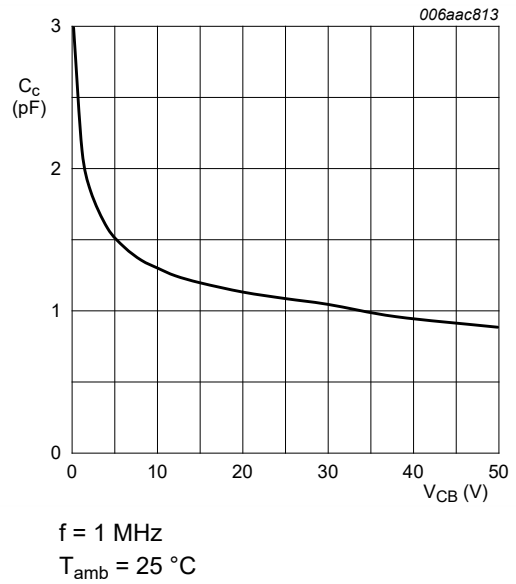


Fig. 15. PDTC123JQC-Q: Collector capacitance as a function of collector-base voltage; typical values

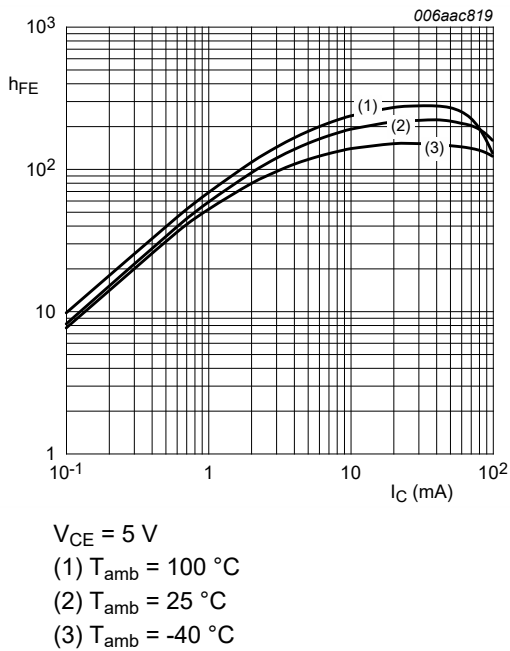


Fig. 16. PDTC143ZQC-Q: DC current gain as a function of collector current; typical values

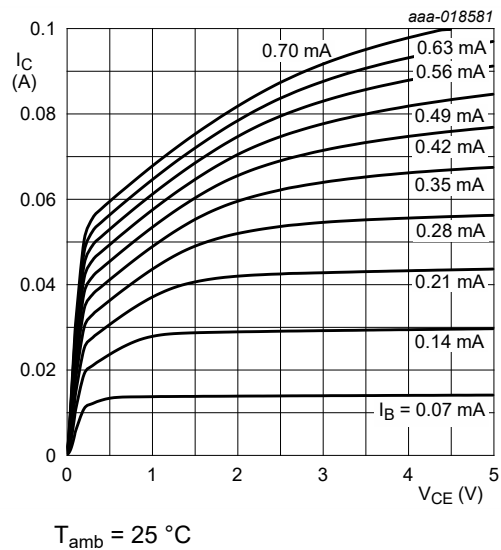
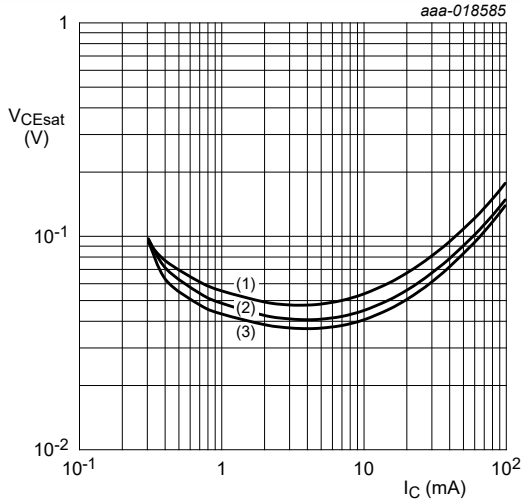


Fig. 17. PDTC143ZQC-Q: Collector current as a function of collector-emitter voltage; typical values

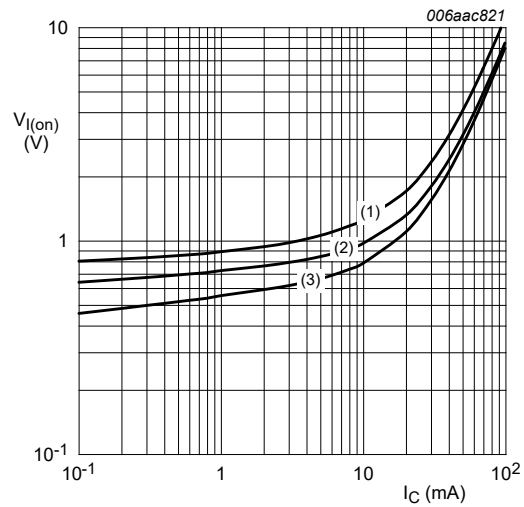
50 V, 100 mA NPN resistor-equipped transistors



$I_C/I_B = 20$

- (1) $T_{amb} = 100\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -40\text{ °C}$

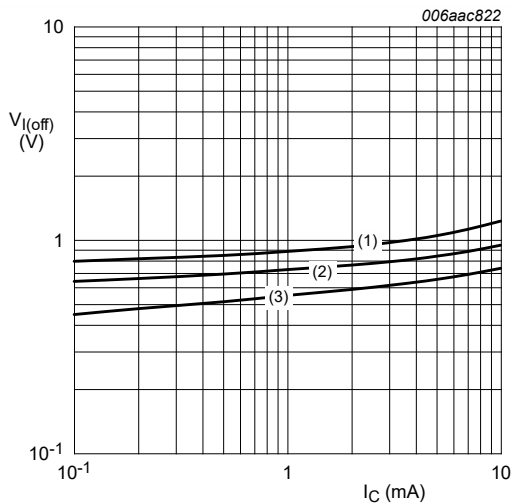
Fig. 18. PDTC143ZQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.3\text{ V}$

- (1) $T_{amb} = -40\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

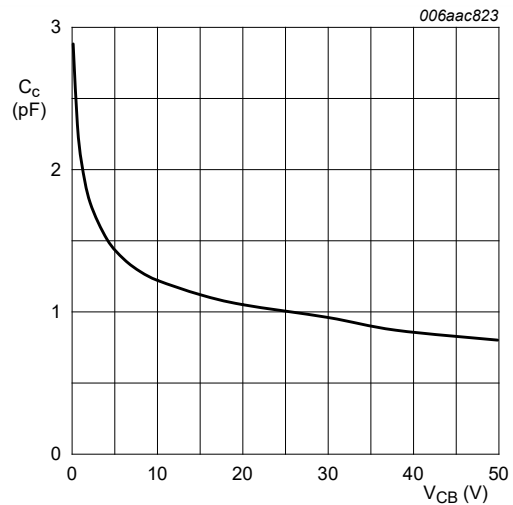
Fig. 19. PDTC143ZQC-Q: On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$

- (1) $T_{amb} = -40\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

Fig. 20. PDTC143ZQC-Q: Off-state input voltage as a function of collector current; typical values



$f = 1\text{ MHz}$

$T_{amb} = 25\text{ °C}$

Fig. 21. PDTC143ZQC-Q: Collector capacitance as a function of collector-base voltage; typical values

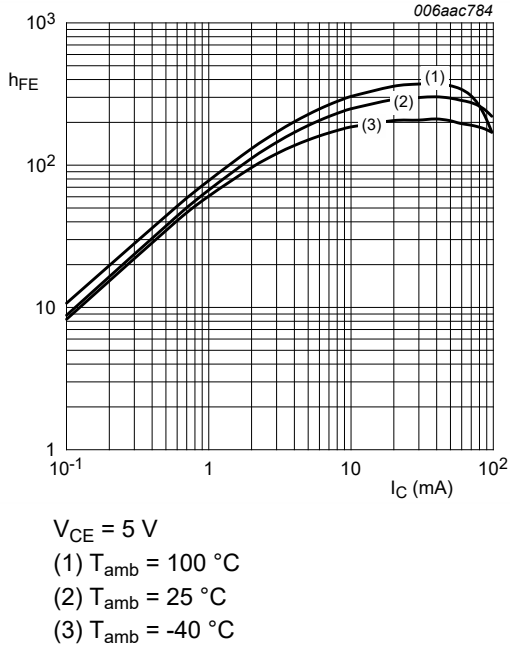


Fig. 22. PDTC114YQC-Q: DC current gain as a function of collector current; typical values

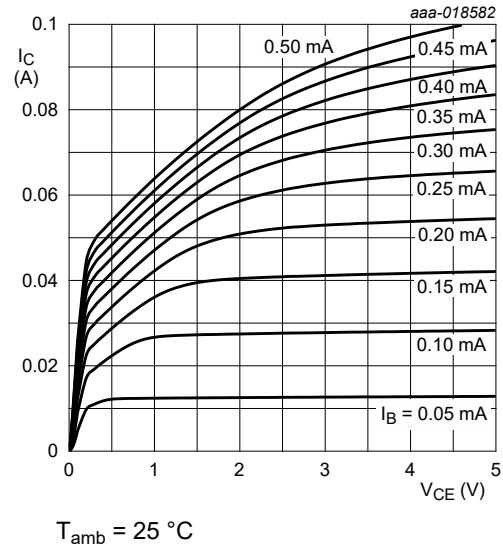


Fig. 23. PDTC114YQC-Q: Collector current as a function of collector-emitter voltage; typical values

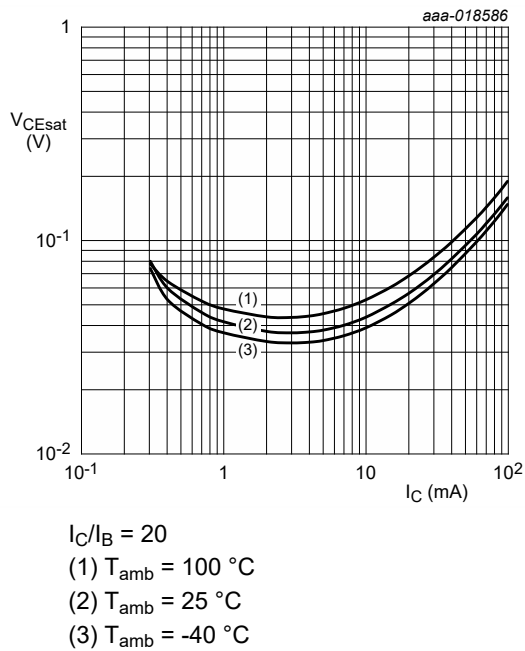


Fig. 24. PDTC114YQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values

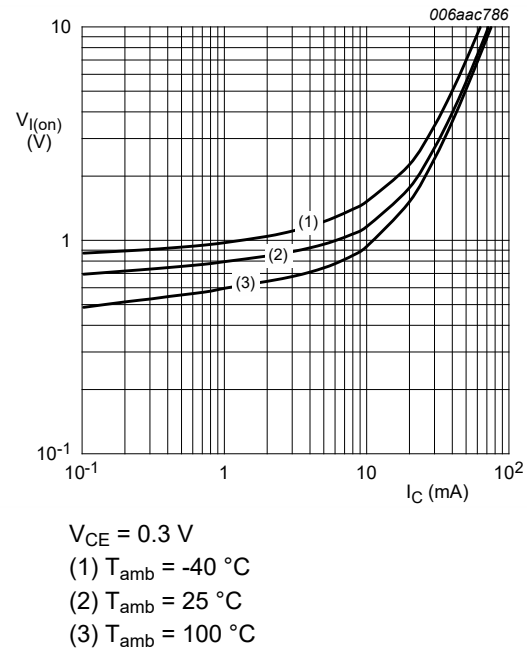


Fig. 25. PDTC114YQC-Q: On-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN resistor-equipped transistors

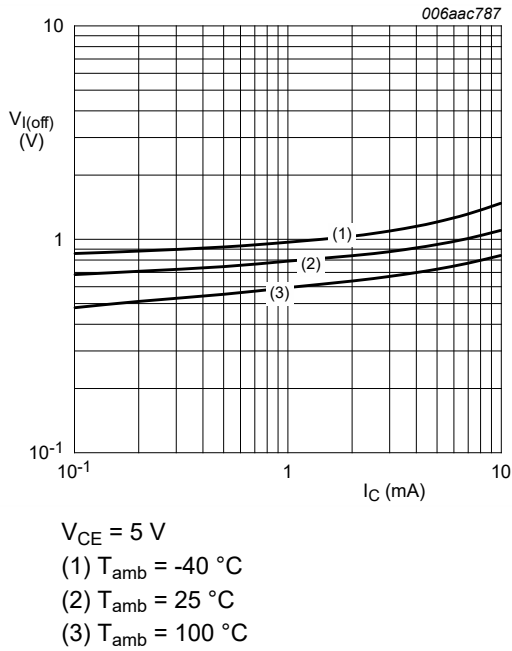


Fig. 26. PDTC114YQC-Q: Off-state input voltage as a function of collector current; typical values

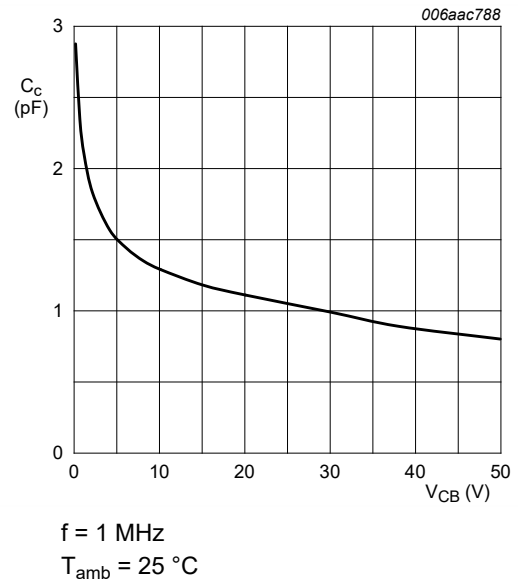


Fig. 27. PDTC114YQC-Q: Collector capacitance as a function of collector-base voltage; typical values

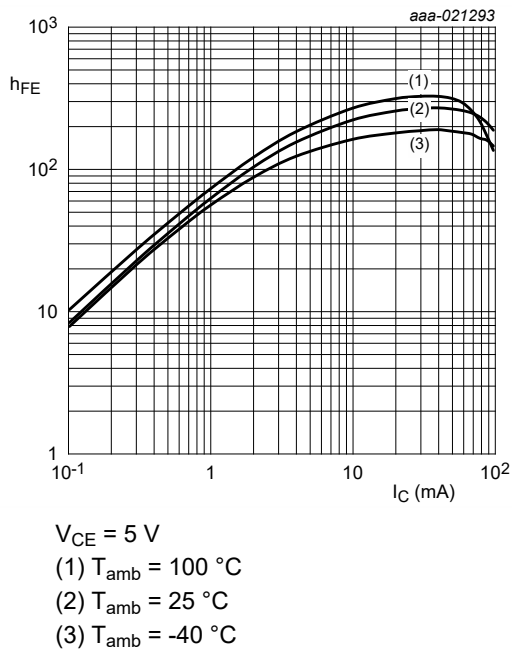


Fig. 28. PDTC124XQC-Q: DC current gain as a function of collector current; typical values

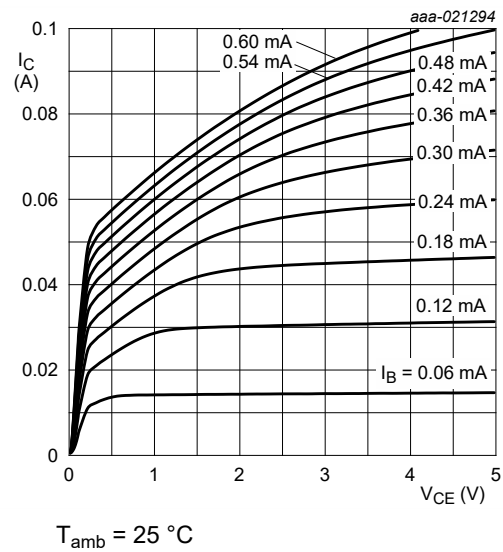
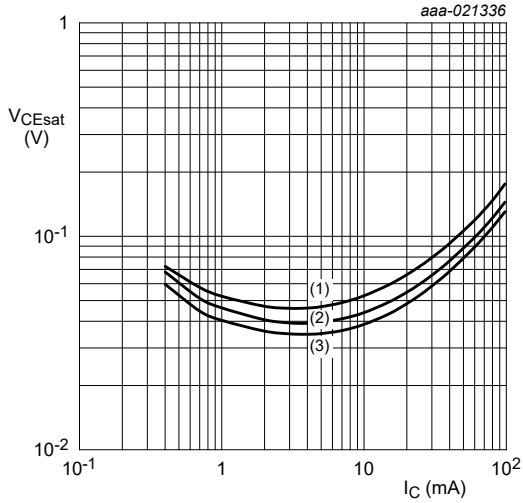


Fig. 29. PDTC124XQC-Q: Collector current as a function of collector-emitter voltage; typical values

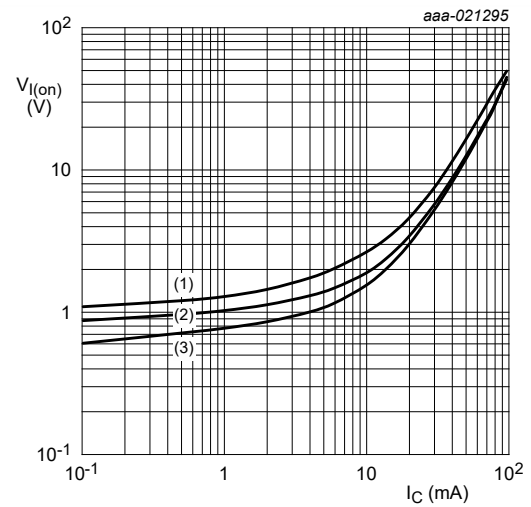
50 V, 100 mA NPN resistor-equipped transistors



$I_C/I_B = 20$

- (1) $T_{amb} = 100\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -40\text{ °C}$

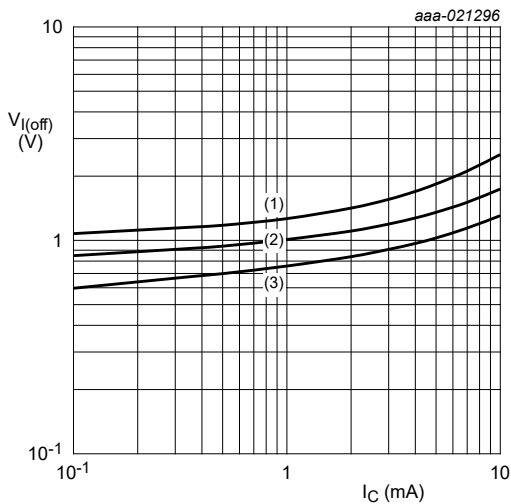
Fig. 30. PDTC124XQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = 0.5\text{ V}$

- (1) $T_{amb} = -40\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

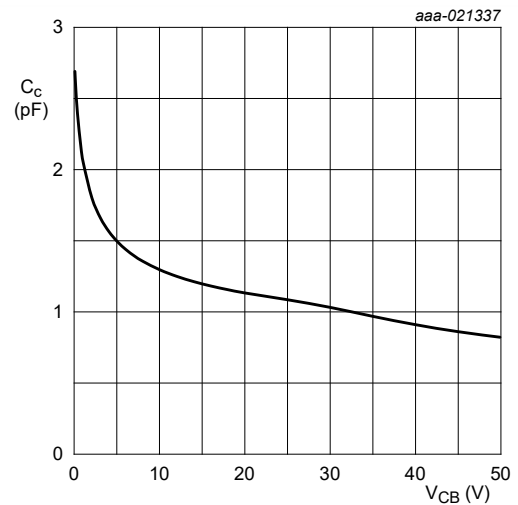
Fig. 31. PDTC124XQC-Q: On-state input voltage as a function of collector current; typical values



$V_{CE} = 5\text{ V}$

- (1) $T_{amb} = -40\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 100\text{ °C}$

Fig. 32. PDTC124XQC-Q: Off-state input voltage as a function of collector current; typical values

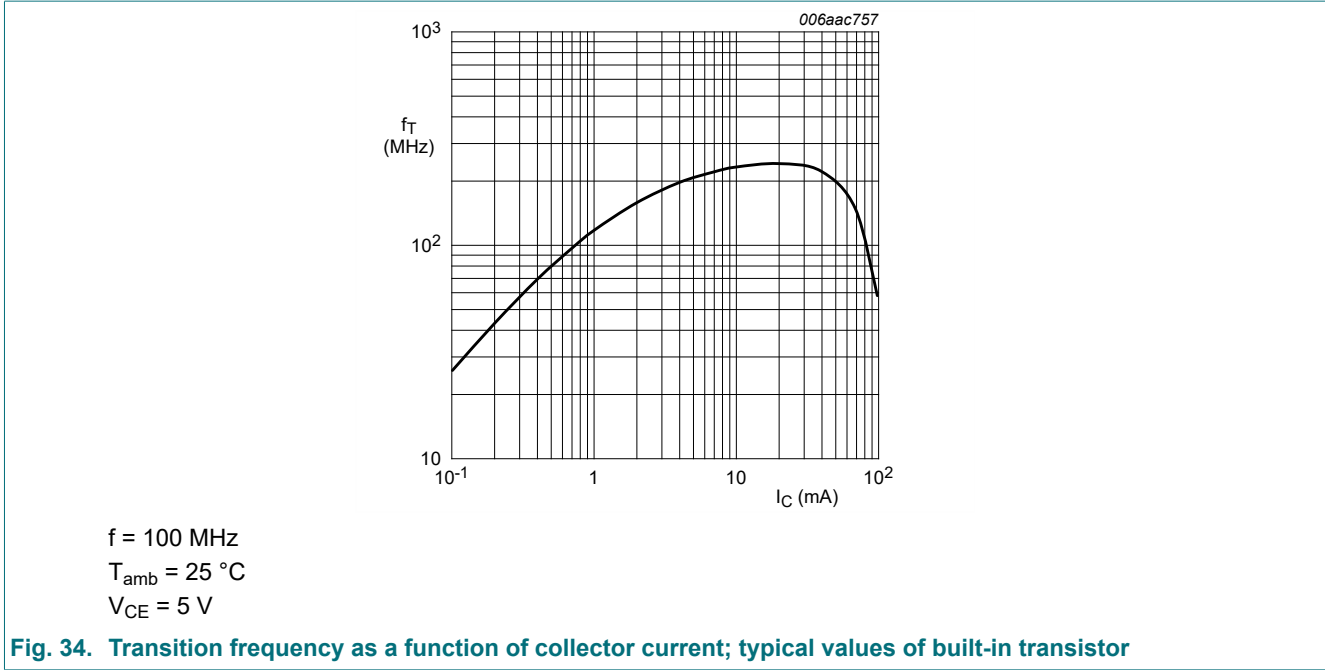


$f = 1\text{ MHz}$

$T_{amb} = 25\text{ °C}$

Fig. 33. PDTC124XQC-Q: Collector capacitance as a function of collector-base voltage; typical values

50 V, 100 mA NPN resistor-equipped transistors



11. Test information

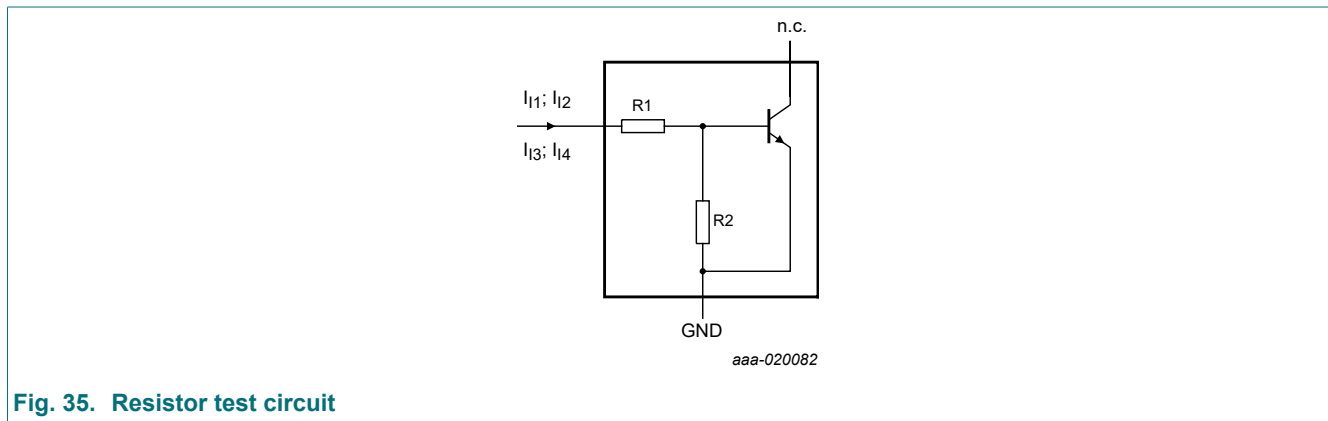
Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

- Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$



Resistor test conditions

Table 9. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁₁	I ₁₂	I ₁₃	I ₁₄
PDTC143XQC-Q	4.7	10	350 μA	450 μA	-350 μA	-450 μA
PDTC123JQC-Q	2.2	47	90 μA	140 μA	-55 μA	-105 μA
PDTC143ZQC-Q	4.7	47	90 μA	140 μA	-55 μA	-105 μA
PDTC114YQC-Q	10	47	90 μA	140 μA	-55 μA	-105 μA
PDTC124XQC-Q	22	47	55 μA	105 μA	-55 μA	-105 μA

11.1. Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

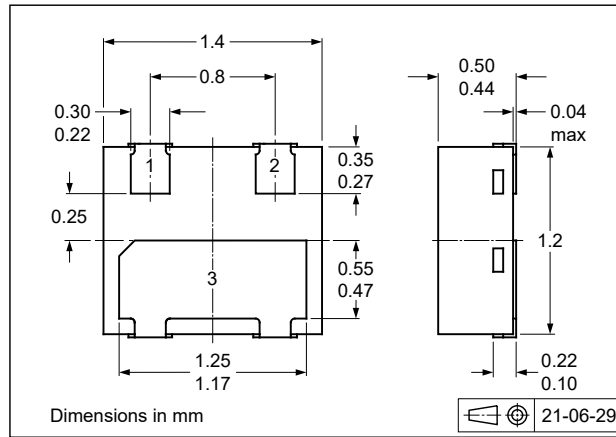
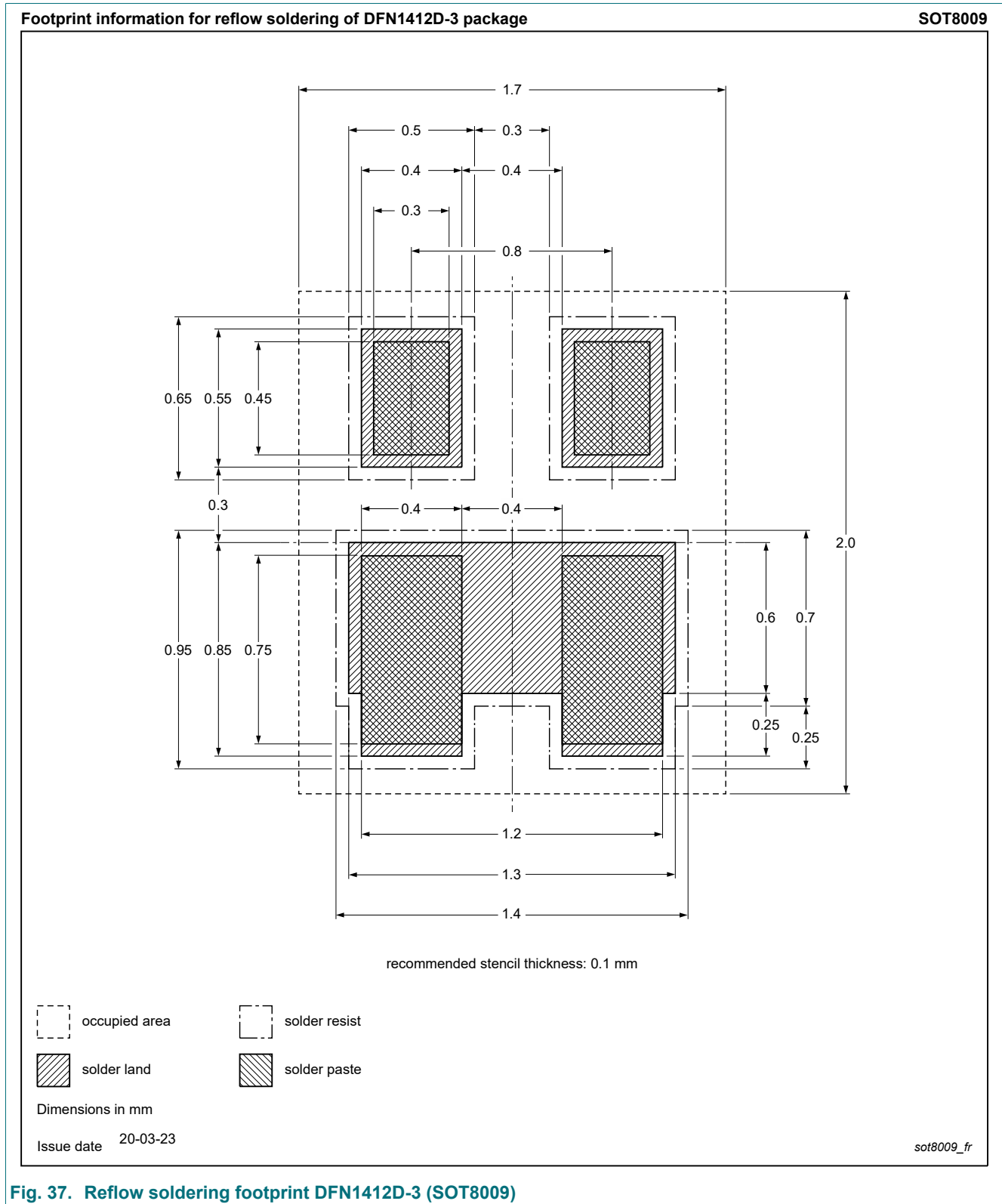


Fig. 36. Package outline DFN1412D-3 (SOT8009)

13. Soldering



14. Revision history

Table 10. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PDTC143X_to_124XQC-Q_SER v.1	20211001	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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50 V, 100 mA NPN resistor-equipped transistors

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